MSD1819A-RT1G, NSVMSD1819A-RT1G

General Purpose Amplifier Transistor

NPN Silicon Surface Mount

This NPN Silicon Epitaxial Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- High h_{FE}, 210-460
- Low V_{CE(sat)}, < 0.5 V
- Moisture Sensitivity Level 1
- ESD Protection:
 - ♦ Human Body Model > 4000 V
 - ◆ Machine Model > 400 V
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	7.0	Vdc
Collector Current – Continuous	Ic	100	mAdc
Collector Current – Peak	I _{C(P)}	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	P _D	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

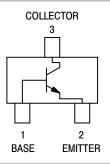


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SC-70 (SOT-323) CASE 419 STYLE 3



MARKING DIAGRAM



ZR = Device Code
M = Date Code*
• Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVMSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MSD1819A-RT1G, NSVMSD1819A-RT1G

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit	
Collector-Emitter Breakdown Voltage (I _C = 2.0 mAdc, I _B = 0)	V _{(BR)CEO}	50	-	Vdc	
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc	
Emitter-Base Breakdown Voltage ($I_E = 10 \mu Adc, I_E = 0$)	V _{(BR)EBO}	7.0	_	Vdc	
Collector-Base Cutoff Current (V _{CB} = 20 Vdc, I _E = 0)	I _{CBO}	-	0.1	μΑ	
Collector-Emitter Cutoff Current (V _{CE} = 10 Vdc, I _B = 0)	I _{CEO}	-	0.1	μΑ	
DC Current Gain (Note 2) ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 2.0 \text{ mAdc}$) ($V_{CE} = 2.0 \text{ Vdc}$, $I_{C} = 100 \text{ mAdc}$)	h _{FE1} h _{FE2}	210 90	340 -	-	
Collector-Emitter Saturation Voltage (Note 2) (I _C = 100 mAdc, I _B = 10 mAdc)	V _{CE(sat)}	_	0.5	Vdc	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

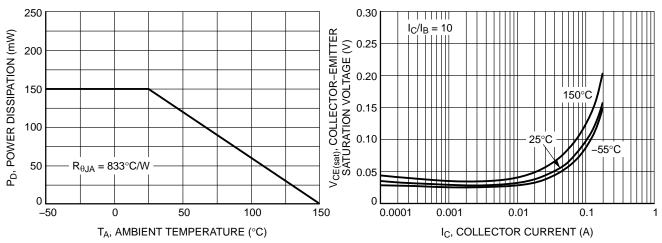


Figure 1. Derating Curve

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

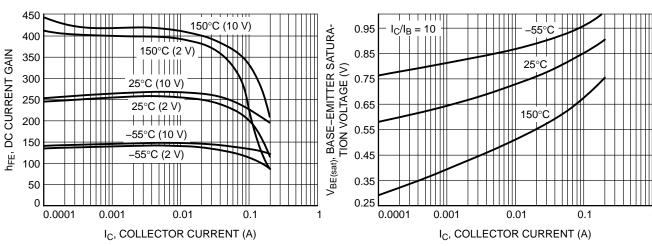
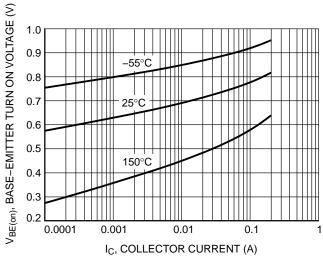


Figure 3. DC Current Gain vs. Collector Current

Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

^{2.} Pulse Test: Pulse Width \leq 300 μ s, D.C. \leq 2%.

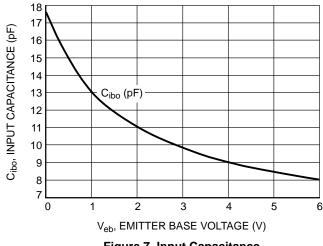
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V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) 1.2 1.0 = 100 mA50 mA 10 mA 0.8 0.6 0.4 0.2 0.000001 0.00001 0.0001 0.001 IB, BASE CURRENT (A)

Figure 5. Base Emitter Turn-On Voltage vs. **Collector Current**

Figure 6. Collector Saturation Region



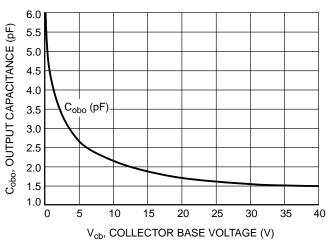


Figure 7. Input Capacitance

Figure 8. Output Capacitance

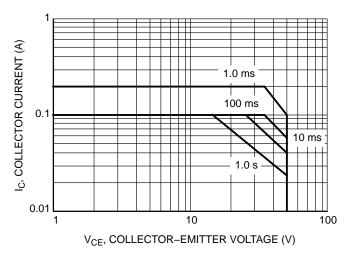
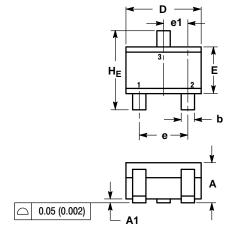


Figure 9. Safe Operating Area

MSD1819A-RT1G, NSVMSD1819A-RT1G

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04



ISSUE N

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

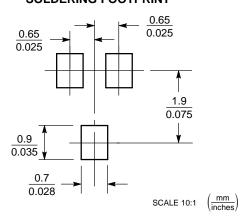
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	;
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



STYLE 3

- PIN 1. BASE
- 2. EMITTER

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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